

45A, 60V, 0.028 Ohm, Logic Level N-Channel Power MOSFETs

These are N-Channel enhancement mode power MOSFETs manufactured using the latest manufacturing process technology. This process, which uses feature sizes approaching those of LSI circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers, and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA49177.

Ordering Information

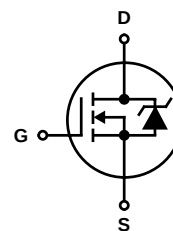
PART NUMBER	PACKAGE	BRAND
RFP45N06LE	TO-220AB	FP45N06L
RF1S45N06LESM	TO-263AB	F45N06LE

NOTE: When ordering, use the entire part number. Add the suffix 9A to obtain the TO-263AB variant in tape and reel i.e., RF1S45N06LESM9A.

Features

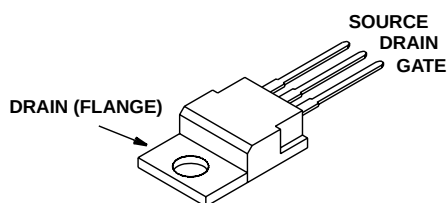
- 45A, 60V
- $r_{DS(ON)} = 0.028\Omega$
- Temperature Compensating PSPICE® Model
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- 175°C Operating Temperature
- Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol

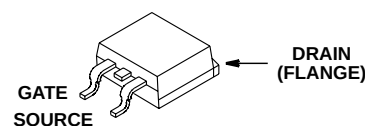


Packaging

JEDEC TO-220AB



JEDEC TO-263AB



RFP45N06LE, RF1S45N06LESM

Absolute Maximum Ratings $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

	RFP45N06LE, RF1S45N06LESM	UNITS
Drain to Source Voltage (Note 1)	V_{DSS} 60	V
Drain to Gate Voltage ($R_{GS} = 20\text{k}\Omega$) (Note 1)	V_{DGR} 60	V
Gate to Source Voltage	V_{GS} ± 10	V
Continuous Drain Current	I_D 45	A
Pulsed Drain Current (Note 3)	I_{DM} Refer to Peak Current Curve	
Pulsed Avalanche Rating	E_{AS} Refer to UIS Curve	
Power Dissipation	P_D 142	W
Derate Above 25°C	0.95	W/ $^{\circ}\text{C}$
Operating and Storage Temperature	T_J, T_{STG} -55 to 175	$^{\circ}\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s	T_L 300	$^{\circ}\text{C}$
Package Body for 10s, See Techbrief 334	T_{pkg} 260	$^{\circ}\text{C}$

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}\text{C}$ to 150°C .

Electrical Specifications $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$ (Figure 13)	60	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$ (Figure 12)	1	-	3	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 55\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
		$V_{DS} = 50\text{V}$, $V_{GS} = 0\text{V}$, $T_C = 150^{\circ}\text{C}$	-	-	250	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 10\text{V}$	-	-	10	μA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = 45\text{A}$, $V_{GS} = 5\text{V}$ (Figure 11)	-	-	0.028	Ω
Turn-On Time	t_{ON}	$V_{DD} = 30\text{V}$, $I_D = 45\text{A}$, $R_L = 0.67\Omega$, $V_{GS} = 5\text{V}$, $R_{GS} = 2.5\Omega$ (Figures 10, 18, 19)	-	-	215	ns
Turn-On Delay Time	$t_{d(ON)}$		-	20	-	ns
Rise Time	t_r		-	150	-	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	55	-	ns
Fall Time	t_f		-	90	-	ns
Turn-Off Time	t_{OFF}		-	-	185	ns
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 48\text{V}$, $I_D = 45\text{A}$, $R_L = 1.07\Omega$ (Figures 20, 21)	107	135	nC
Gate Charge at 5V	$Q_{g(5)}$	$V_{GS} = 0\text{V}$ to 5V		58	75	nC
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0\text{V}$ to 1V		2.4	3.0	nC
Input Capacitance	C_{ISS}	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$ (Figure 14)	-	2150	-	pF
Output Capacitance	C_{OSS}		-	640	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	240	-	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	1.05	$^{\circ}\text{C/W}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	TO-220, and TO-263	-	-	80	$^{\circ}\text{C/W}$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 45\text{A}$	-	-	1.5	V
Diode Reverse Recovery Time	t_{rr}	$I_{SD} = 45\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	155	ns

NOTES:

2. Pulse test: pulse width $\leq 80\mu\text{s}$, duty cycle $\leq 2\%$.
3. Repetitive rating: pulse width limited by Max junction temperature. See Transient Thermal Impedance curve (Figure 3).

Typical Performance Curves Unless Otherwise Specified

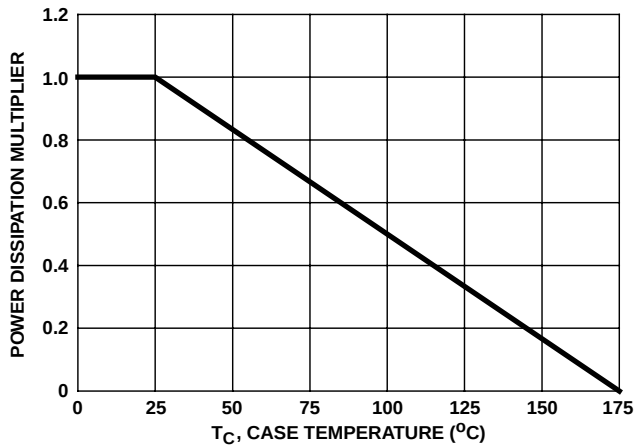


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

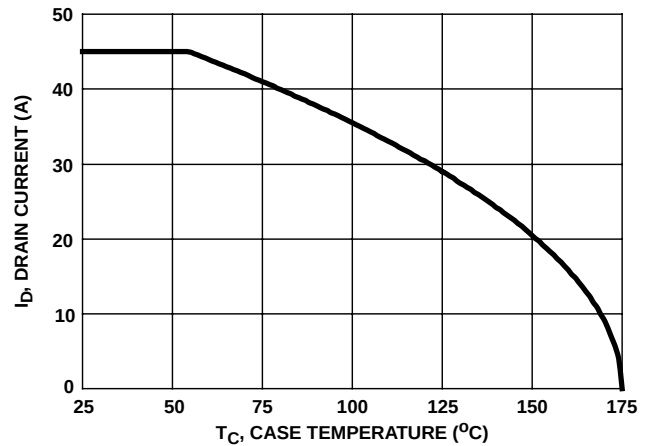


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

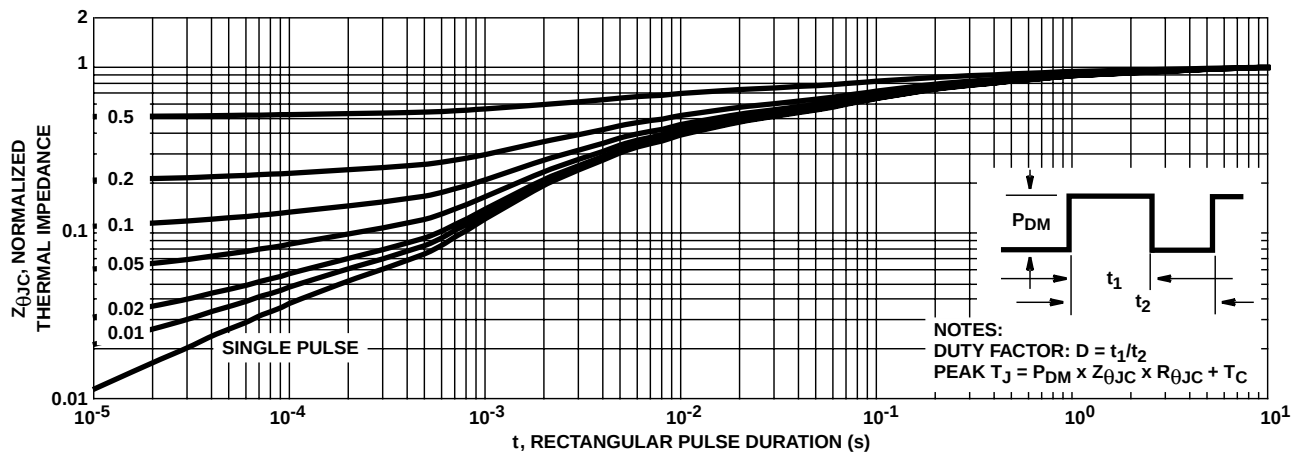


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

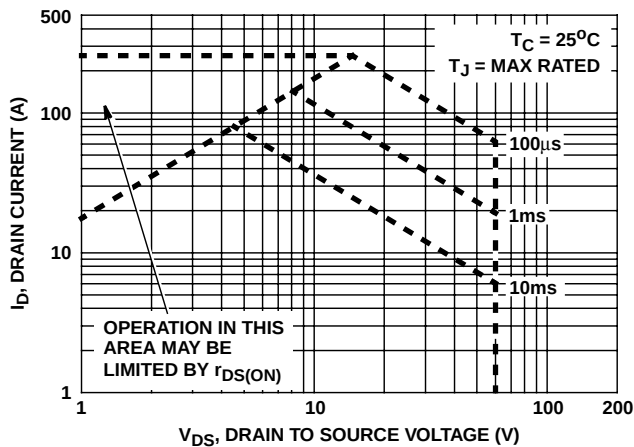


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

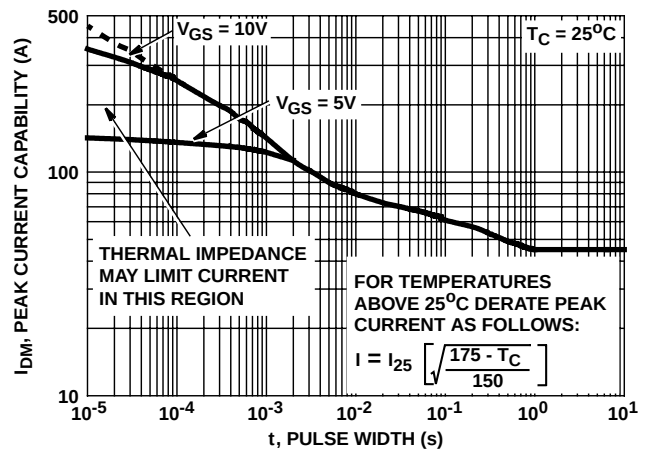
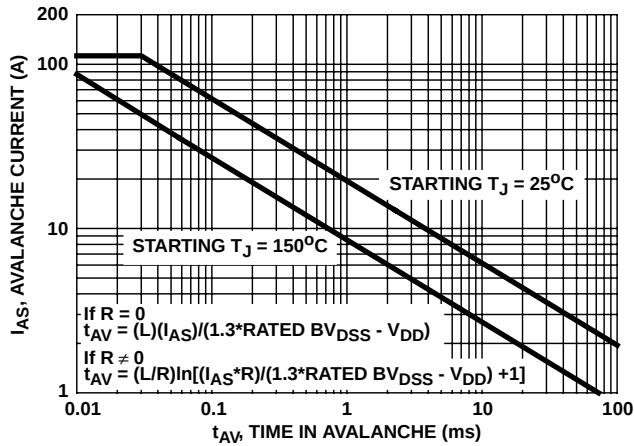


FIGURE 5. PEAK CURRENT CAPABILITY

Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Intersil Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

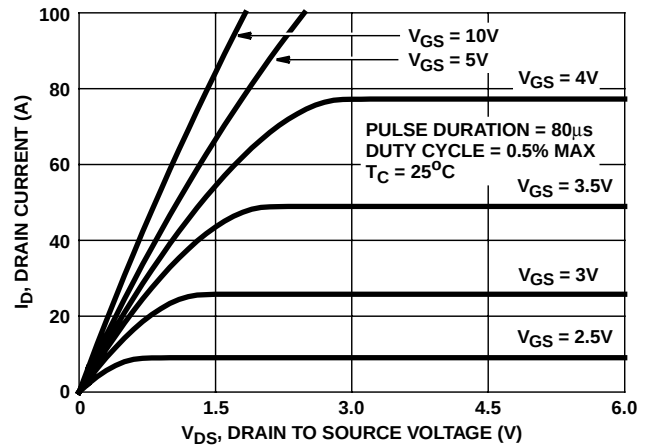


FIGURE 7. SATURATION CHARACTERISTICS

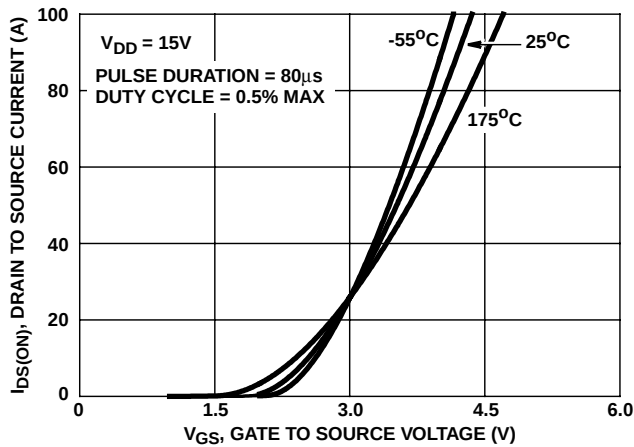


FIGURE 8. TRANSFER CHARACTERISTICS

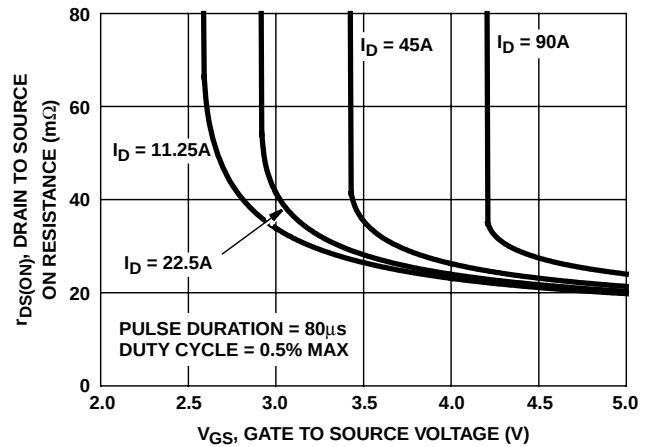


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

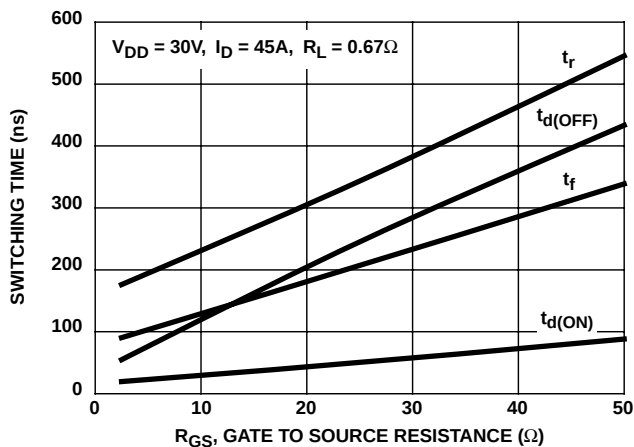


FIGURE 10. SWITCHING TIME vs GATE RESISTANCE

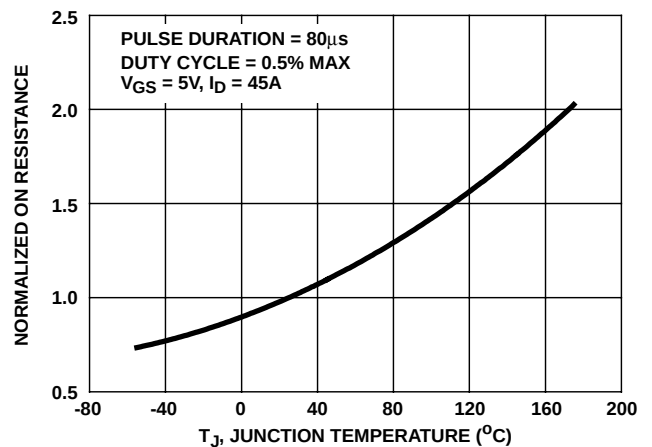


FIGURE 11. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

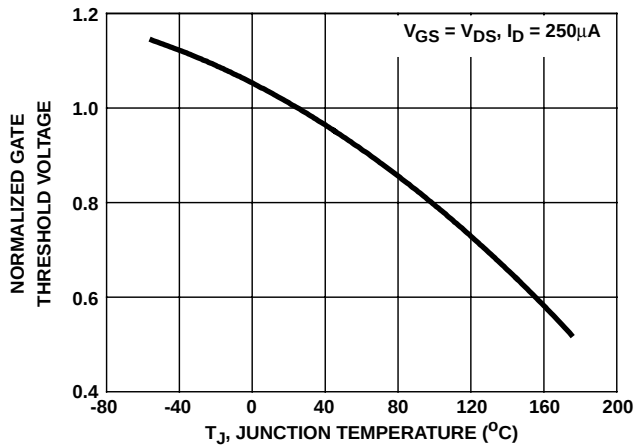


FIGURE 12. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

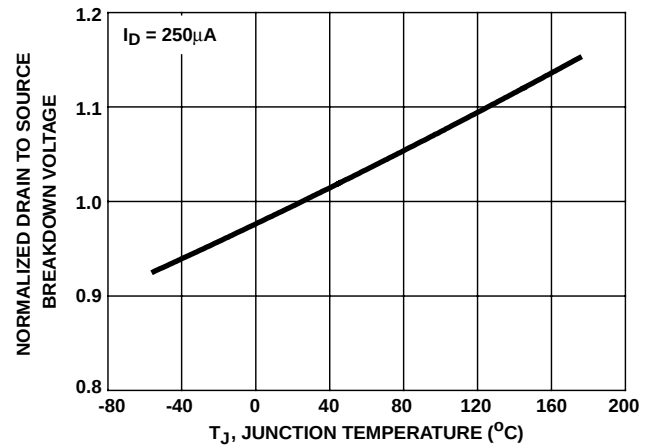


FIGURE 13. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

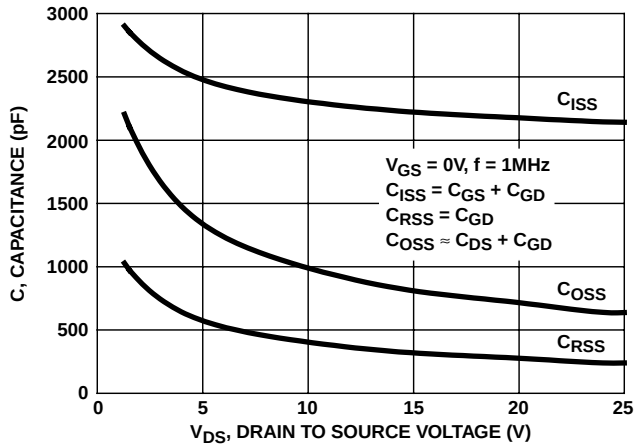
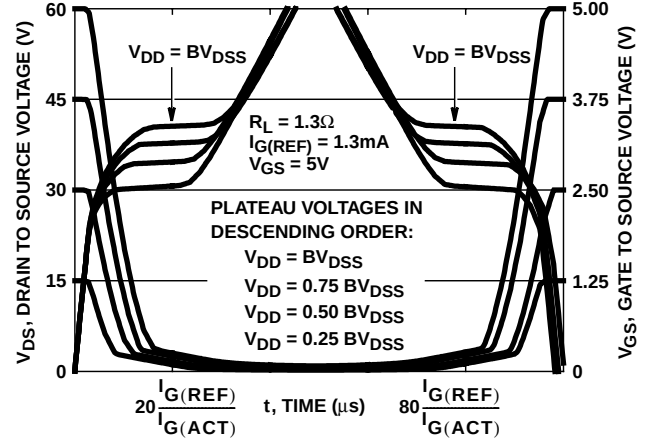


FIGURE 14. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Intersil Application Notes AN7254 and AN7260.

FIGURE 15. NORMALIZED SWITCHING WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

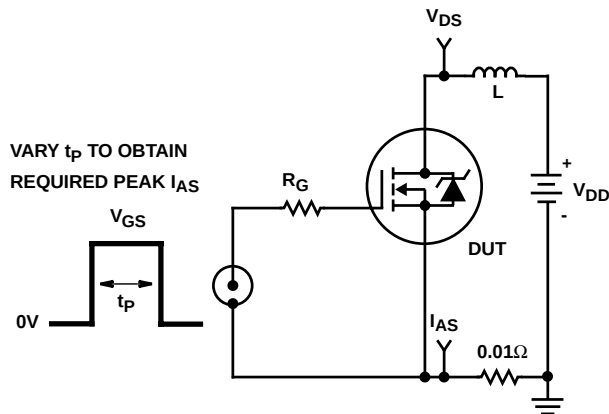


FIGURE 16. UNCLAMPED ENERGY TEST CIRCUIT

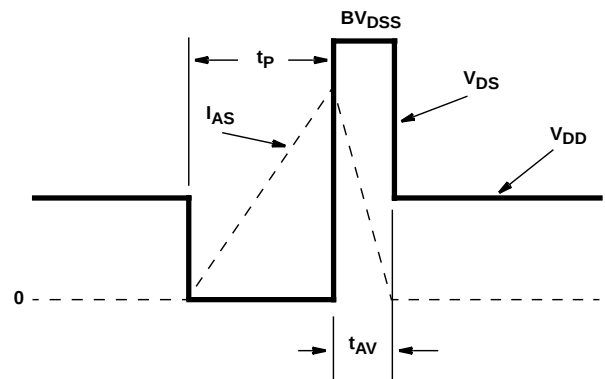


FIGURE 17. UNCLAMPED ENERGY WAVEFORMS

Test Circuits and Waveforms (Continued)

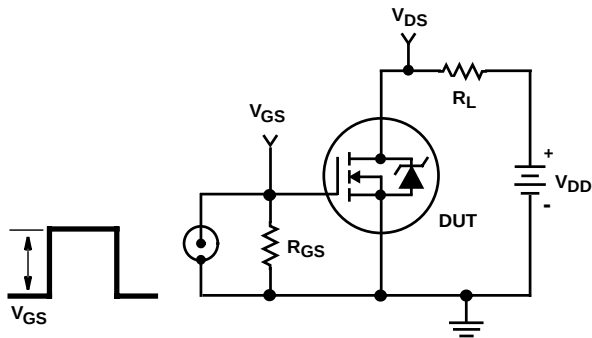


FIGURE 18. SWITCHING TIME TEST CIRCUIT

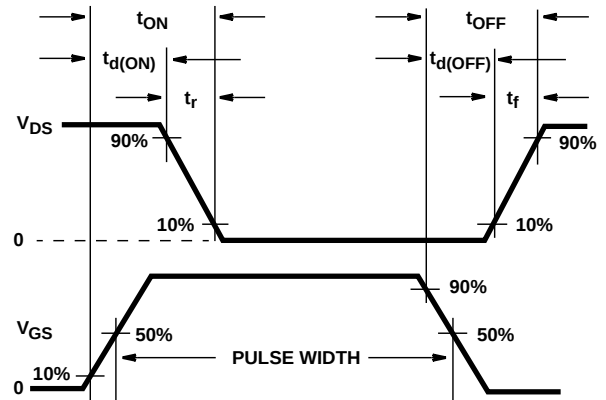


FIGURE 19. RESISTIVE SWITCHING WAVEFORMS

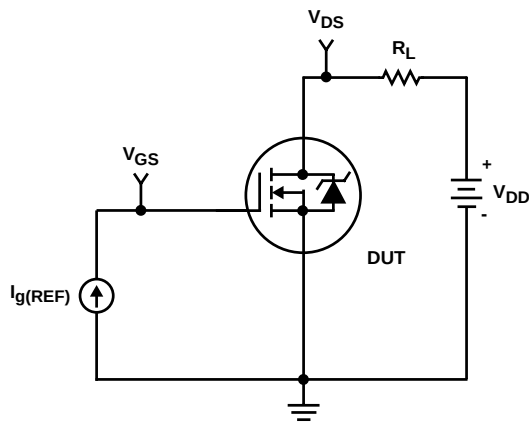


FIGURE 20. GATE CHARGE TEST CIRCUIT

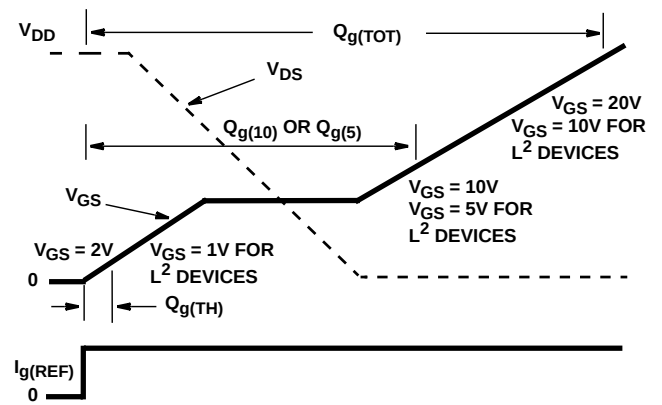


FIGURE 21. GATE CHARGE WAVEFORMS

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